

Silicon Epitaxial Planar Diode

Low leakage switching diode

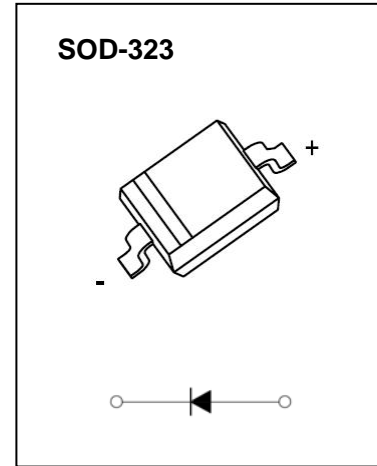
Features

- Plastic SMD package
- Low leakage current

Application

- Low leakage current applications in surface mounted circuits.

MARKING: JV



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$t = 1\ \mu\text{s}$	4
		$t = 1\ \text{ms}$	1
		$t = 1\ \text{s}$	0.5
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

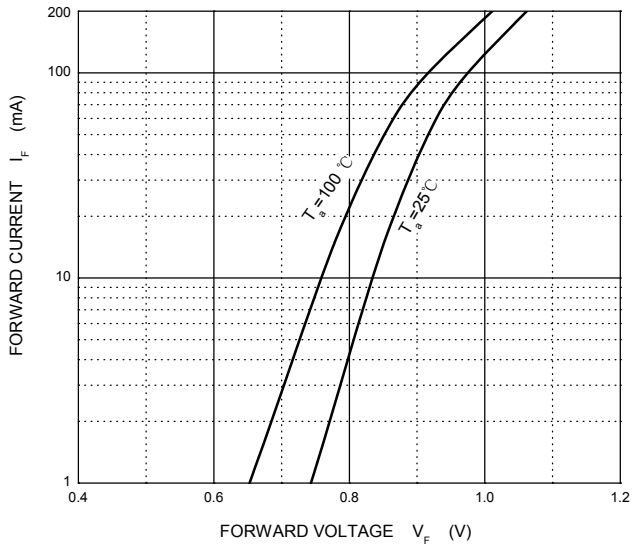
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage	V_F	-	at $I_F = 1\ \text{mA}$	0.9
			at $I_F = 10\ \text{mA}$	1
			at $I_F = 50\ \text{mA}$	1.1
			at $I_F = 150\ \text{mA}$	1.25
Reverse Current	I_R	-	at $V_R = 75\ \text{V}$	5
			at $V_R = 75\ \text{V}, T_j = 150\text{ }^\circ\text{C}$	80
Diode Capacitance	C_d	2	-	pF
Reverse Recovery Time	t_{rr}	-	3	μs
at $I_F = I_R = 10\ \text{mA}, R_L = 100\ \Omega, i_{rr} = 0.1\ I_R$				

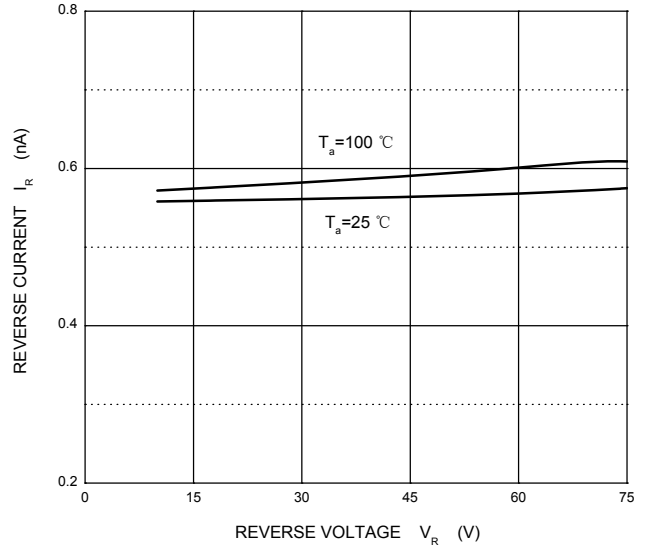


Typical Characteristics

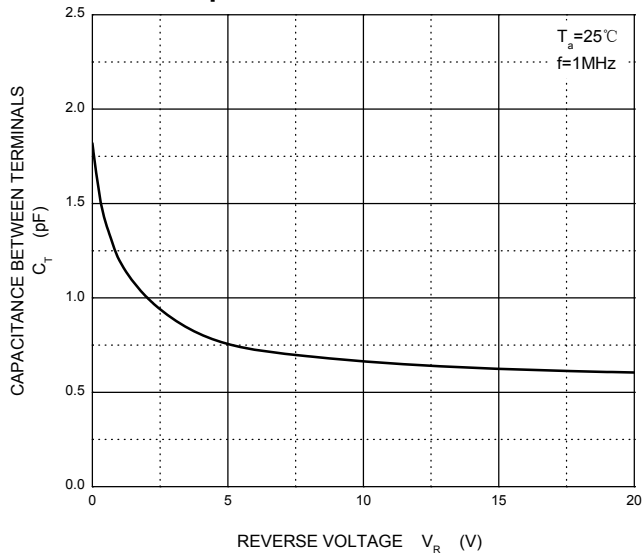
Forward Characteristics



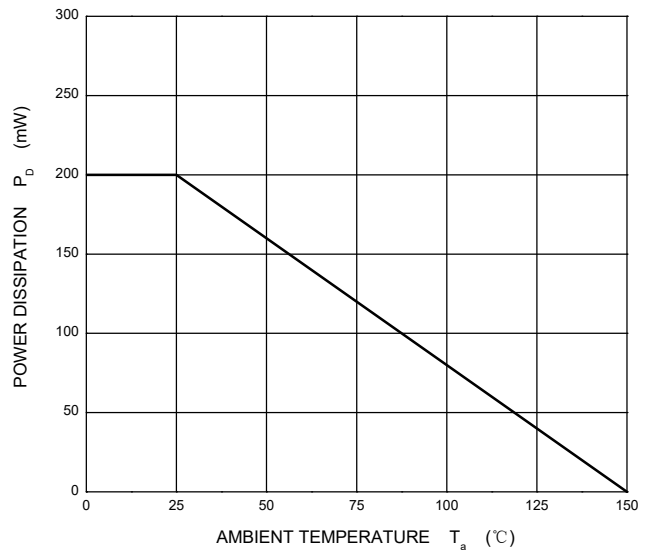
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

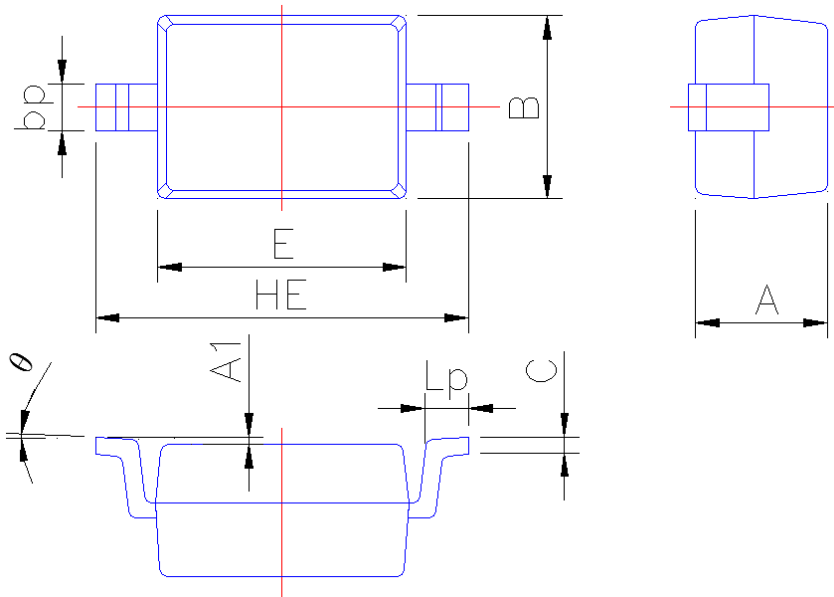




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°